

2N5985 Transistors

Si NPN Power BJT

Military/High-Rel N

$V_{(BR)CEO}$ (V) 80

$V_{(BR)CBO}$ (V) 100

I_C Max. (A) 8.0

Absolute Max. Power Diss. (W) 90#

Maximum Operating Temp ($^{\circ}C$) 150 \bar{o}

I_{CBO} Max. (A) 1.0m $^{\circ}$

@ V_{CBO} (V) (Test Condition) 40

$V_{(CE)sat}$ Max. (V) 1.7

@ I_C (A) (Test Condition) 8.0

@ I_B (A) (Test Condition) 1.2

$h_{(FE)}$ Min. Current gain. 20

$h_{(FE)}$ Max. Current gain. 120

@ I_C (A) (Test Condition) 4.0

@ V_{CE} (V) (Test Condition) 2.0

f_T Min. (Hz) Transition Freq 2.0M

@ I_C (A) (Test Condition) 500m

@ V_{CE} (V) (Test Condition) 10

t_d Max. (s) Delay time.

t_r Max. (s) Rise time

t_{on} Max. (s) On time.